

## **isc** Silicon NPN Power Transistor

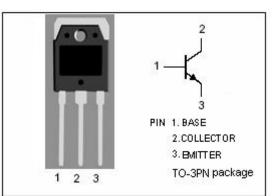
# 2SC3680

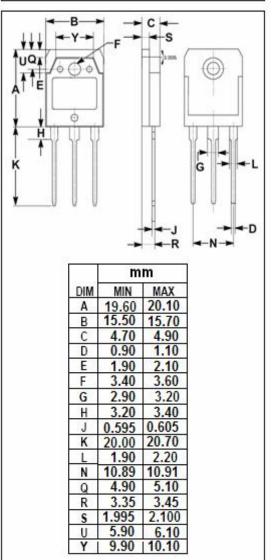
### DESCRIPTION

- High Collector-Emitter Breakdown Voltage-: V<sub>(BR)CEO</sub>= 800V(Min)
- High Switching Speed
- High Reliability
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

• Designed for switching regulator and general purpose applications.





## ABSOLUTE MAXIMUM RATINGS(Ta=25 °C)

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	900	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V	
V <sub>EBO</sub>	Emitter-Base voltage	7	V	
lc	Collector Current-Continuous	7	A	
Ісм	Collector Current-Peak	14	A	
I <sub>B</sub>	Base Current-Continuous	3.5	A	
Pc	Collector Power Dissipation @ $T_c=25^{\circ}C$	120	W	
TJ	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	



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## **ELECTRICAL CHARACTERISTICS**

#### $T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT	
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	800			V	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			0.5	V	
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 3A; I <sub>B</sub> = 0.6A			1.2	V	
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 800V; I <sub>E</sub> = 0			0.1	mA	
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			0.1	mA	
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 3A; V <sub>CE</sub> = 4V	10		30		
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>E</sub> = -2A; V <sub>CE</sub> = 12V		6		MHz	
Сов	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1.0MHz		105		pF	
Switching times							
t <sub>on</sub>	Turn-on Time				1.0	μ <b>S</b>	

lon	Turn-on time			1.0	μ3
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 3A, I <sub>B1</sub> = 0.45A; I <sub>B2</sub> = -1.5A R <sub>L</sub> = 83 Ω; V <sub>CC</sub> = 250V		5.0	μs
tf	Fall Time			1.0	μ <b>S</b>

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